



DONGGUAN NANJING ELECTRONICS LTD.,
SOT-223 Plastic-Encapsulate Transistors

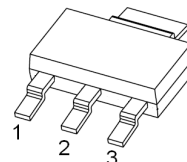
PZT3904 TRANSISTOR (NPN)

FEATURES

- Low Voltage and Low Current
- Complementary to PZT3906
- General Purpose Amplifier and Switch Application

SOT-223

1. BASE
2. COLLECTOR
3. EMITTER



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.01\text{mA}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.01\text{mA}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			50	nA
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{EB}=3\text{V}$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			50	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65		0.85	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz
Collector output capacitance	C_{ob}	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$			4	pF
Delay time	t_d	$V_{CC}=3\text{V}, V_{BE(off)}=0.5\text{V}, I_C=10\text{mA}, I_{B1}=-I_{B2}=1\text{mA}$			35	ns
Rise time	t_r				35	
Storage time	t_s	$V_{CC}=3\text{V}, I_C=10\text{mA}, I_{B1}=-I_{B2}=1\text{mA}$			200	ns
Fall time	t_f				50	